

Product Overview

NGTB30N60IHLWG: IGBT, Field Stop (FS), 30 A, 600 V

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for half bridge resonant applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Low Saturation Voltage using Trench with Fieldstop Technology
- Low Switching Loss

Benefits

- Low Conduction Loss
- Reduces System Power Dissipation

Applications

- Half Bridge IH

End Products

- Inductive Heating Hobs

Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_r Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μ s)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Pack aged Diode	Package Type
NGTB30N60IHLWG	Pb-free	Active	600	30	1.8	1.2	0.28		400	23	130			250	Yes	TO-247-3
	Halide free															

For more information please contact your local sales support at www.onsemi.com.

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